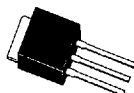
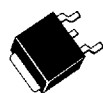


2SJ189



2083A



2092A

LD (Low Drive) Series $V_{DS}=30V$

P Channel Power MOSFET

©3762A

Features

- Low ON resistance
- Very high-speed switching
- Low-voltage drive

Absolute Maximum Ratings at $T_a=25^\circ C$

Drain to Source Voltage	V_{DS}	-30	V
Gate to Source Voltage	V_{GS}	± 15	V
Drain Current (DC)	I_D	-4	A
Drain Current (Pulse)	I_{DP}	-16	A
Allowable Power Dissipation	P_D	30	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

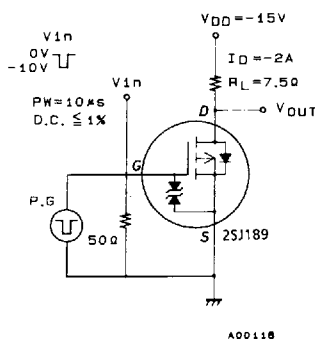
$PW \leq 10\mu s$, duty cycle $\leq 1\%$
 $T_c = 25^\circ C$

Electrical Characteristics at $T_a=25^\circ C$

		min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DS}$	-30			V
G-S Breakdown Voltage	$V_{(BR)GS}$	± 15			V
Zero Gate Voltage Drain Current	I_{DSS}			-100	μA
Gate to Source Leakage Current	I_{GSS}			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	2.5	4		S
Static Drain to Source on State Resistance	$R_{DS(on)}$		85	120	m Ω
	$R_{DS(on)}$		120	170	m Ω
Input Capacitance	C_{iss}		1000		pF
Output Capacitance	C_{oss}		600		pF
Reverse Transfer Capacitance	C_{rss}		220		pF
Turn-ON Delay Time	$t_{d(on)}$		15		ns
Rise Time	t_r		50		ns
Turn-OFF Delay Time	$t_{d(off)}$		145		ns
Fall Time	t_f		145		ns
Diode Forward Voltage	V_{SD}	-1.0	-1.5		V

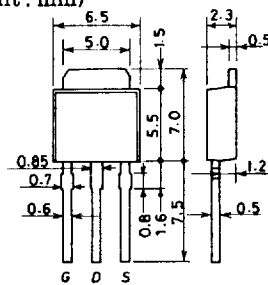
$I_D = -1mA, V_{GS} = 0$
 $I_G = \pm 100\mu A, V_{DS} = 0$
 $V_{DS} = -30V, V_{GS} = 0$
 $V_{GS} = \pm 12V, V_{DS} = 0$
 $V_{DS} = -10V, I_D = -1mA$
 $V_{DS} = -10V, I_D = -2A$
 $I_D = -2A, V_{GS} = -10V$
 $I_D = -2A, V_{GS} = -4V$
 $V_{DS} = -10V, f = 1MHz$
 $V_{DS} = -10V, f = 1MHz$
 $V_{DS} = -10V, f = 1MHz$
 See specified Test Circuit
 $I_S = -4A, V_{GS} = 0$

Switching Time Test Circuit



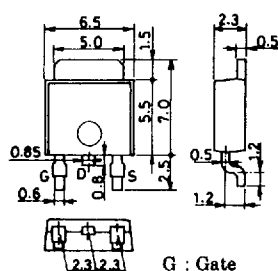
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Package Dimensions 2083A (unit: mm)



G : Gate
 D : Drain
 S : Source
 SANYO : TP

Package Dimensions 2092A (unit: mm)



G : Gate
 D : Drain
 S : Source
 SANYO : TP-FA

